General Description

The WSD30150ADN56 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WSD30150ADN56 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

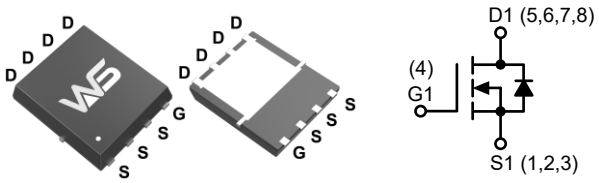
Product Summery

BV_{DSS}	R_{DSON}	I_D
30V	2.2mΩ	145A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,7]	145	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,7]	75	A
I_{DM}	Pulsed Drain Current[2]	310	A
EAS	Single Pulse Avalanche Energy[3]	372	mJ
I_{AS}	Avalanche Current	86	A
P_D@T_C=25℃	Total Power Dissipation[4]	78	W
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	55	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.6	℃/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.022	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	2.2	3.5	mΩ
		V_{GS}=4.5V , I_D=15A	---	3.1	4.2	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.1	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	2	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forwar Trd ansconductance	V_{DS}=5V , I_D=15A	---	32	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.1	2.5	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=20A	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	4.3	---	
Q_{gd}	Gate-Drain Charge		---	8.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GEN}=10V , R_G=6Ω, I_D=1A, R_L=15Ω.	---	11	---	ns
T_r	Rise Time Rise Time		---	16	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
T_f	Turn-Off Fall Time		---	40	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	2450	---	pF
C_{oss}	Output Capacitance		---	590	---	
C_{rss}	Reverse Transfer Capacitance		---	245	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=15A	85	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	50	A
I_{SM}	Pulsed Source Current[2,6]		---	---	310	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=20A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
7.Package limitation current is 100A.

Typical Characteristics

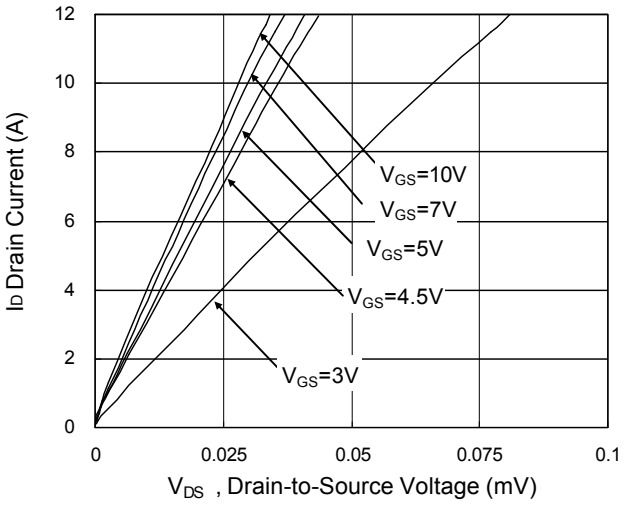


Fig.1 Typical Output Characteristics

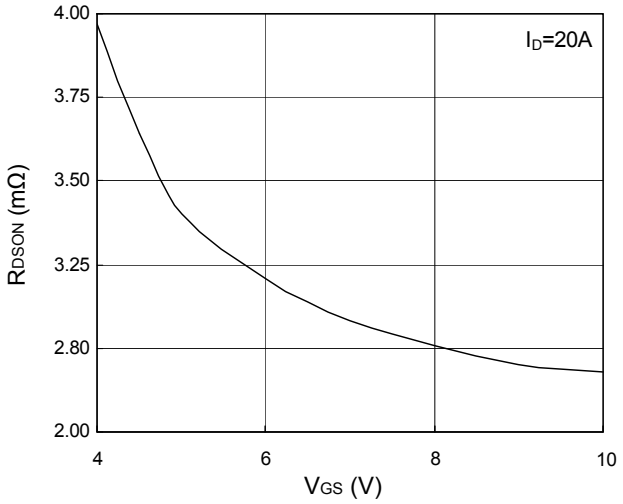


Fig.2 On-Resistance v.s Gate- Source

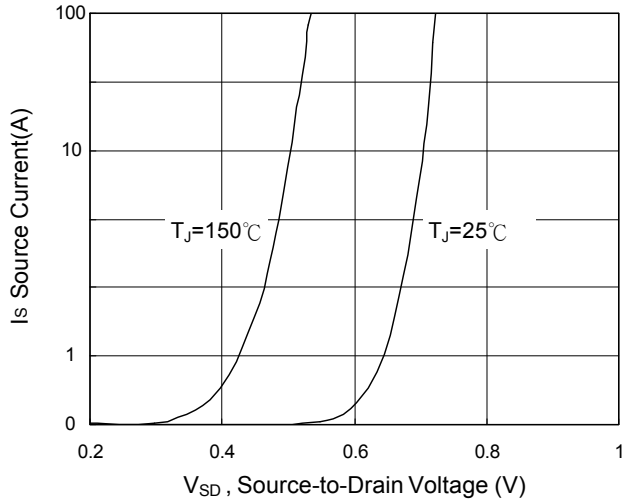


Fig.3 Forward Characteristics of Reverse

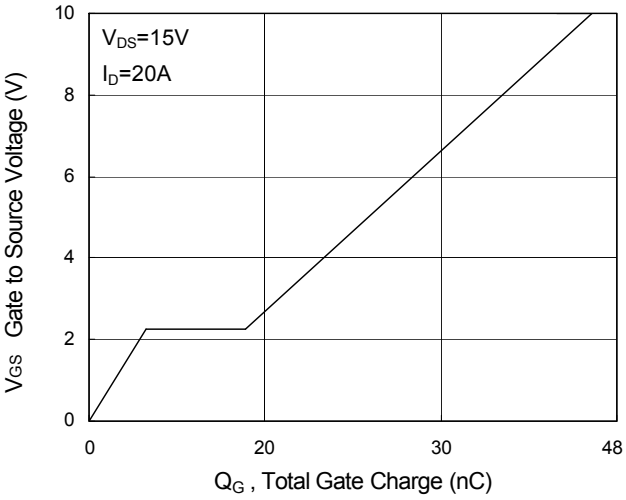


Fig.4 Gate-Charge Characteristics

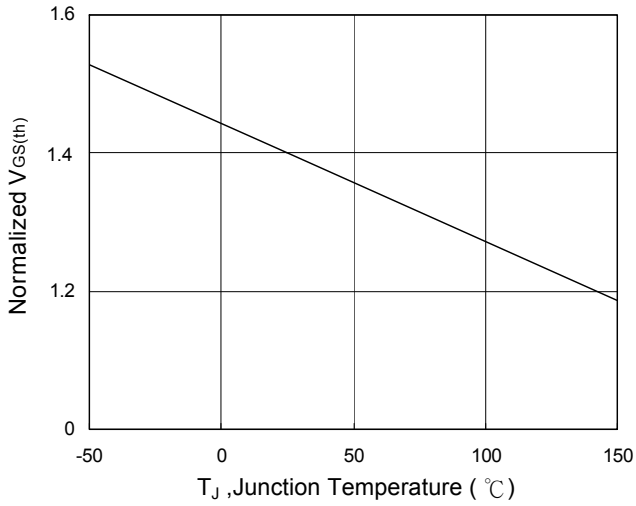


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

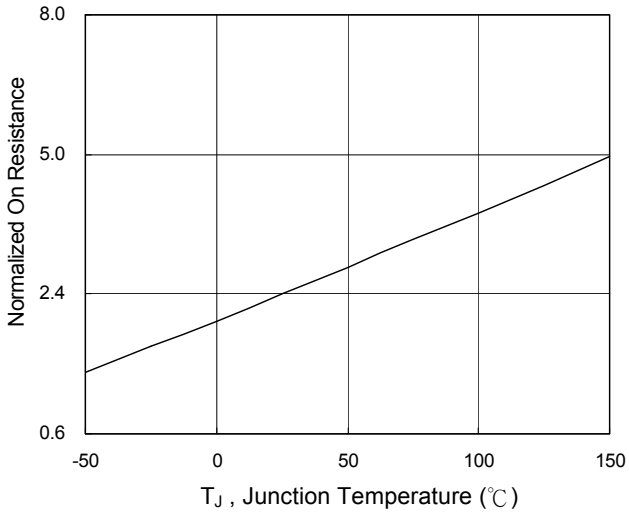


Fig.6 Normalized R_{DSON} v.s T_J

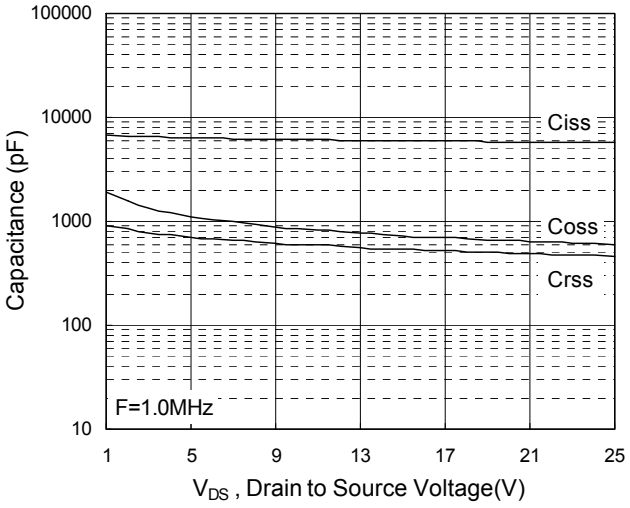


Fig.7 Capacitance

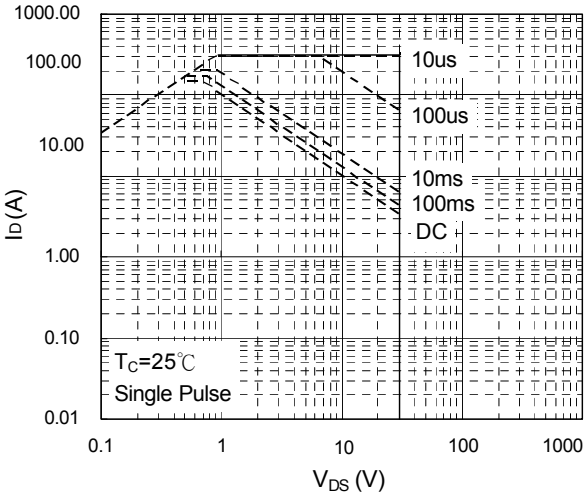


Fig.8 Safe Operating Area

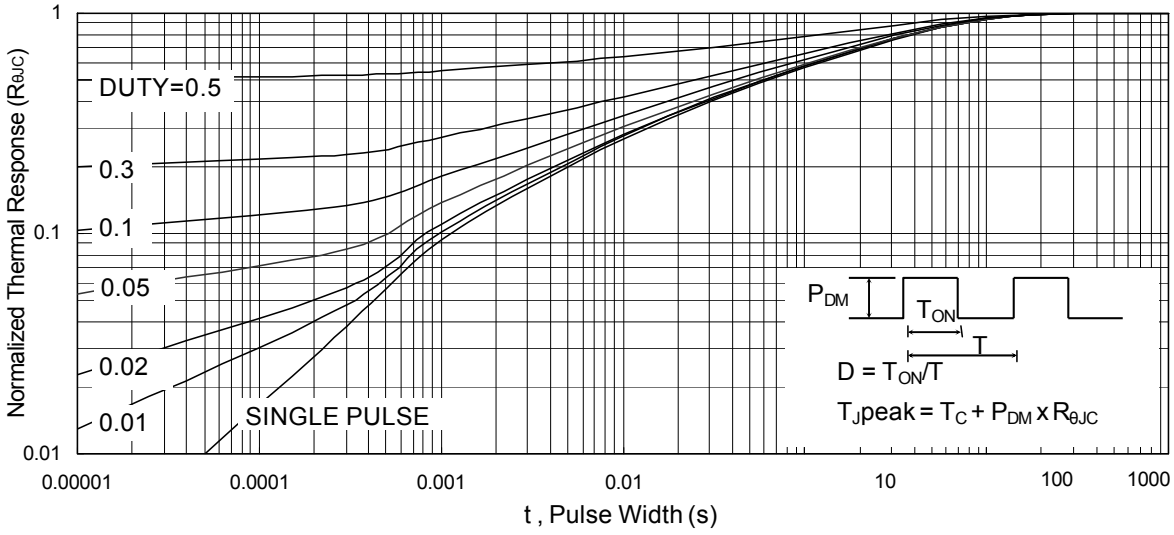


Fig.9 Normalized Maximum Transient Thermal Impedance

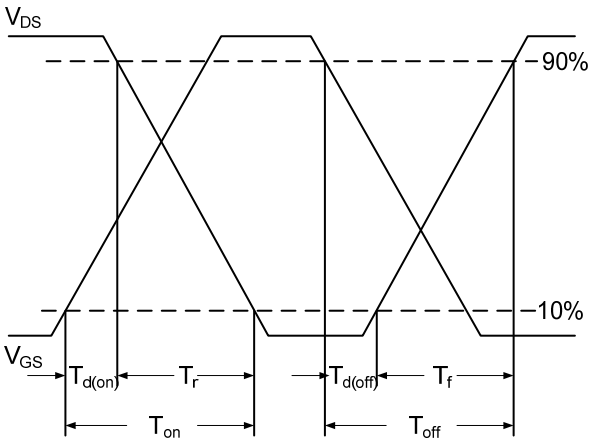


Fig.10 Switching Time Waveform

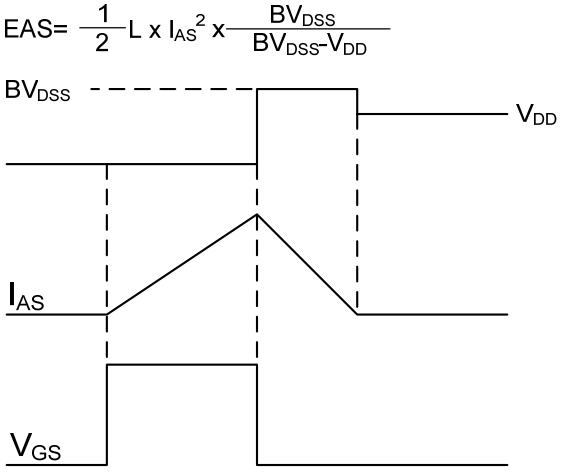
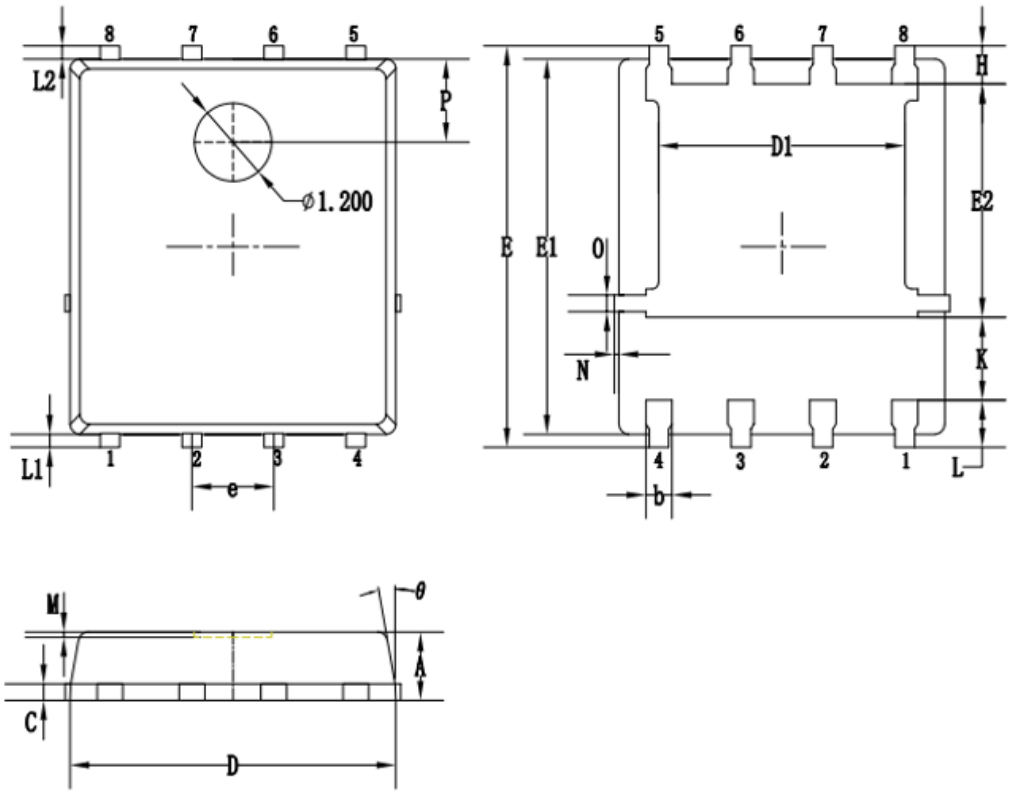


Fig.11 Unclamped Inductive Waveform

Packaging information



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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